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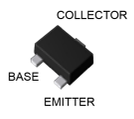
DTA015T series

PNP -100mA -50V Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Value
V_{CEO}	-50V
I_C	-100mA
R_1	100kΩ

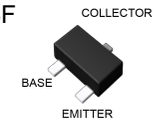
●Outline

VMT3



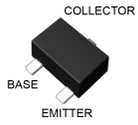
DTA015TM
(SC-105AA)

EMT3F



DTA015TEB
(SC-89)

UMT3F

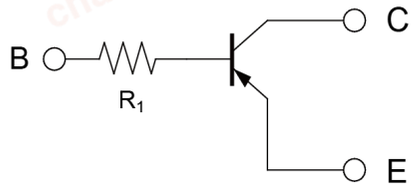


DTA015TUB
(SC-85)

●Features

1) Built-In Biasing Resistor
2) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit) .
3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
4) Only the on/off conditions need to be set for operation, making the circuit design easy.
5) Complementary NPN Types: DTC015T series
6) Lead Free/RoHS Compliant.

●Inner circuit



●Application

Switching circuit, Inverter circuit, Interface circuit, Driver circuit

B: BASE
C: COLLECTOR
E: EMITTER

●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
DTA015TM	VMT3	1212	T2L	180	8	8000	51
DTA015TEB	EMT3F	1616	TL	180	8	3000	51
DTA015TUB	UMT3F	2021	TL	180	8	3000	51

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●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	-50	V
Collector-emitter voltage		V_{CEO}	-50	V
Emitter-base voltage		V_{EBO}	-5	V
Collector current		I_C	-100	mA
Power dissipation	DTA015TM	P_D*1	150	mW
	DTA015TEB		150	
	DTA015TUB		200	
Junction temperature		T_j	150	℃
Range of storage temperature		T_{stg}	-55 to +150	℃

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-base breakdown voltage	BV_{CBO}	I_C = -50μA	-50	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	I_C = -1mA	-50	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I_E = -50μA	-5	-	-	V
Collector cut-off current	I_{CBO}	V_{CB} = -50V	-	-	-0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB} = -4V	-	-	-0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C / I_B = -5mA / -0.25mA	-	-0.05	-0.25	V
DC current gain	h_{FE}	V_{CE} = -10V, I_C = -5mA	100	-	600	-
Input resistance	R_1	-	70	100	130	kΩ
Transition frequency	f_T*2	V_{CE} = -10V, I_E = 5mA, f = 100MHz	-	250	-	MHz

*1 Each terminal mounted on a reference footprint

*2 Characteristics of built-in transistor

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●Electrical characteristic curves (T_a =25°C)

Fig.1 Grounded emitter propagation characteristics

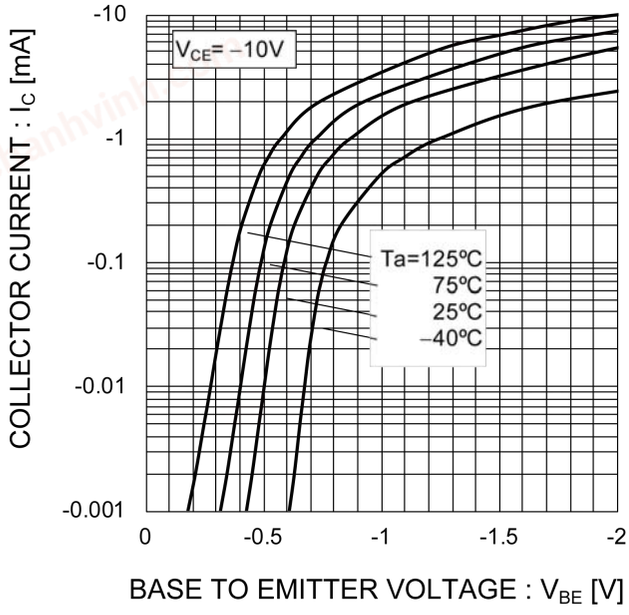


Fig.2 Grounded emitter output characteristics

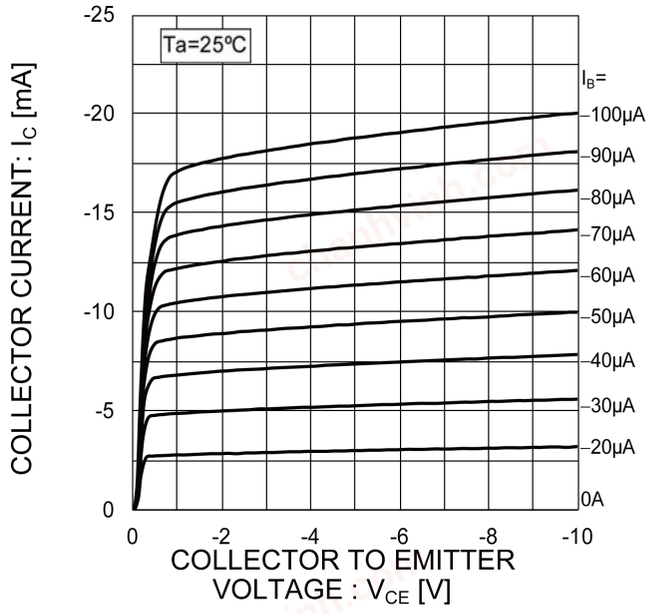


Fig.3 DC Current gain vs. Collector Current

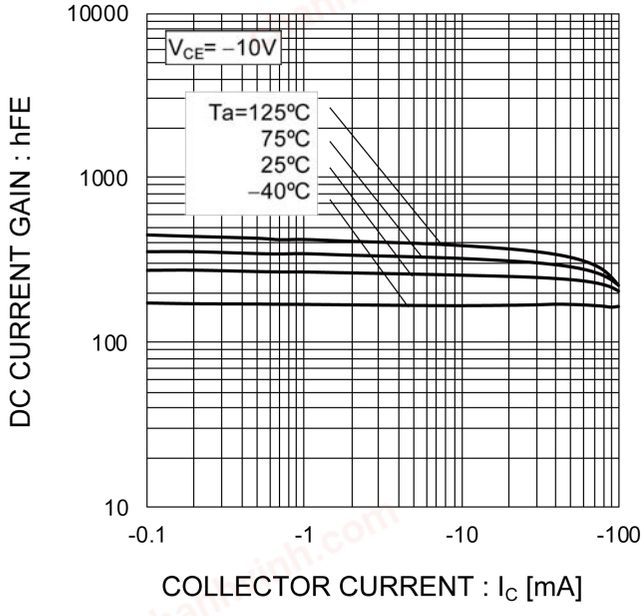
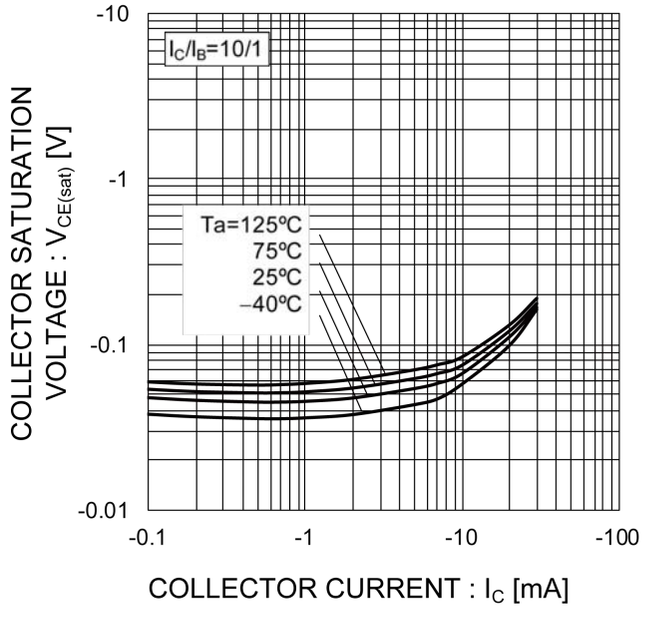


Fig.4 Collector-emitter saturation voltage vs. Collector Current

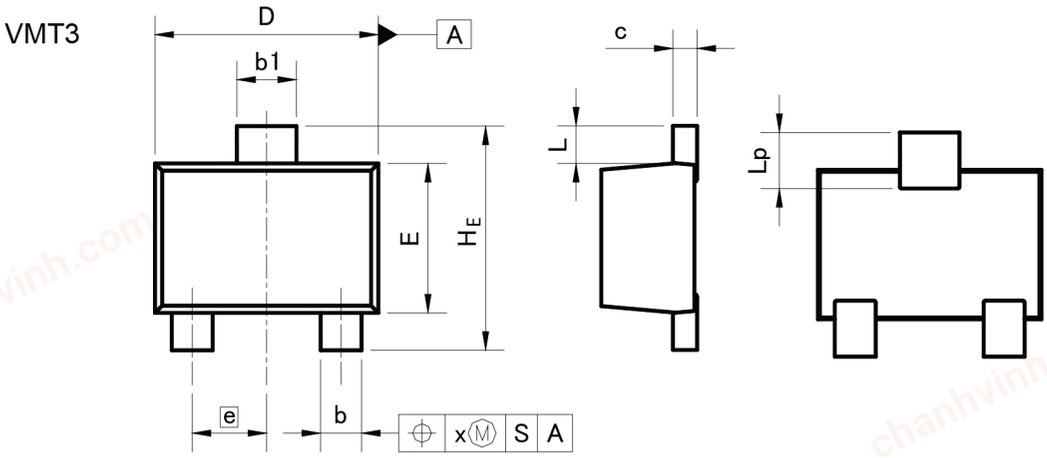


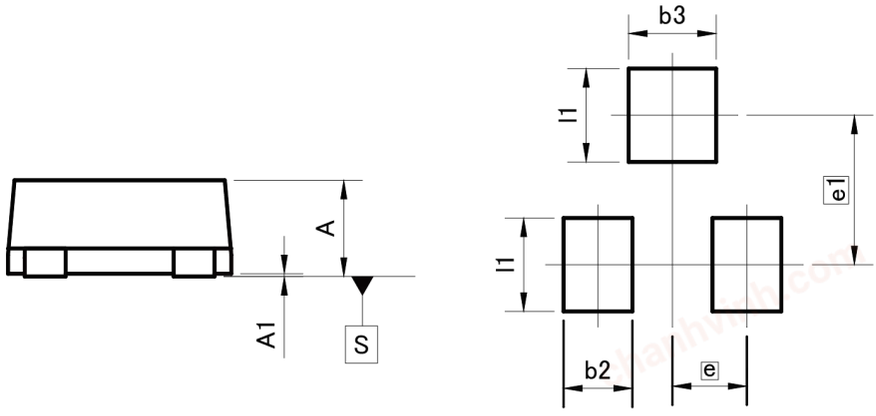
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●Dimensions

VMT3





Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
c	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
e	0.40		0.02	
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
x	−	0.10	−	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	−	0.37	−	0.015
b3	−	0.47	−	0.019
e1	0.80		0.031	
l1	−	0.50	−	0.020

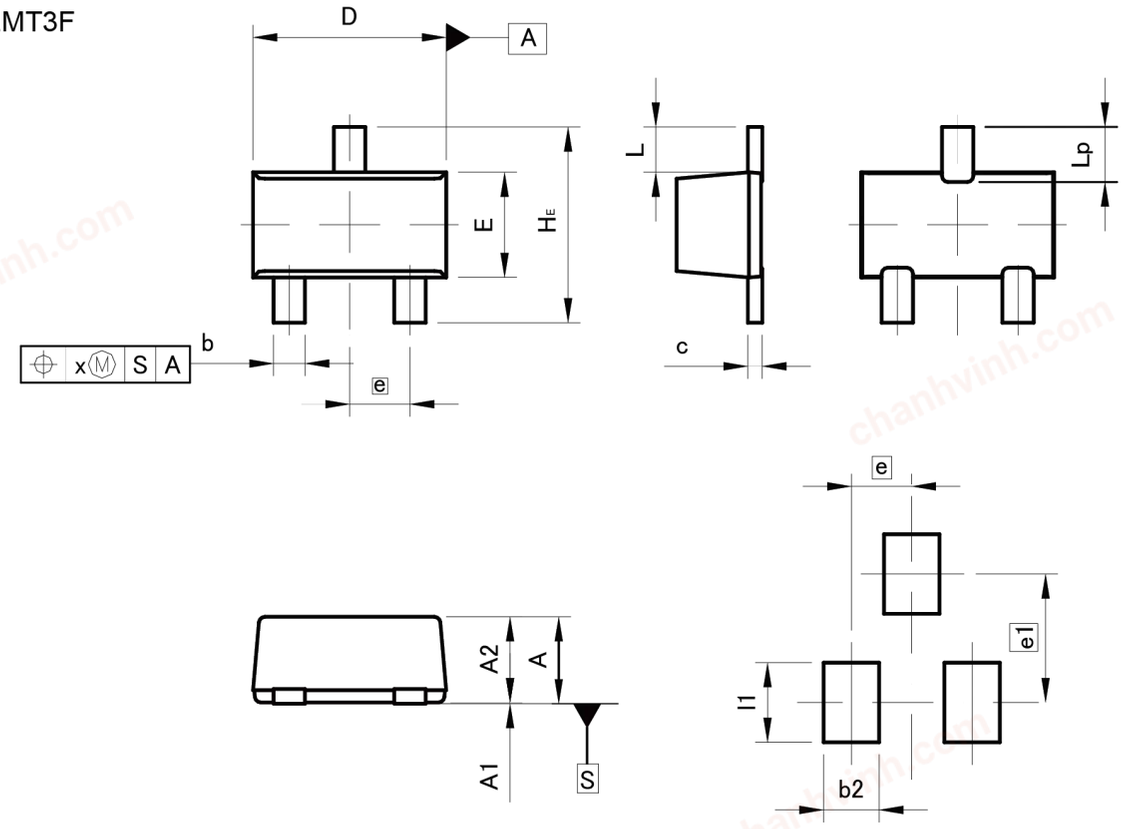
Dimension in mm/inches

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●Dimensions

EMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.030	0.038
e	0.50		0.020	
HE	1.50	1.70	0.059	0.067
L	0.37		0.015	
Lp	0.35	0.55	0.014	0.022
x	−	0.10	−	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	−	0.46	−	0.018
e1	−	1.05	−	0.041
l1	−	0.65	−	0.026

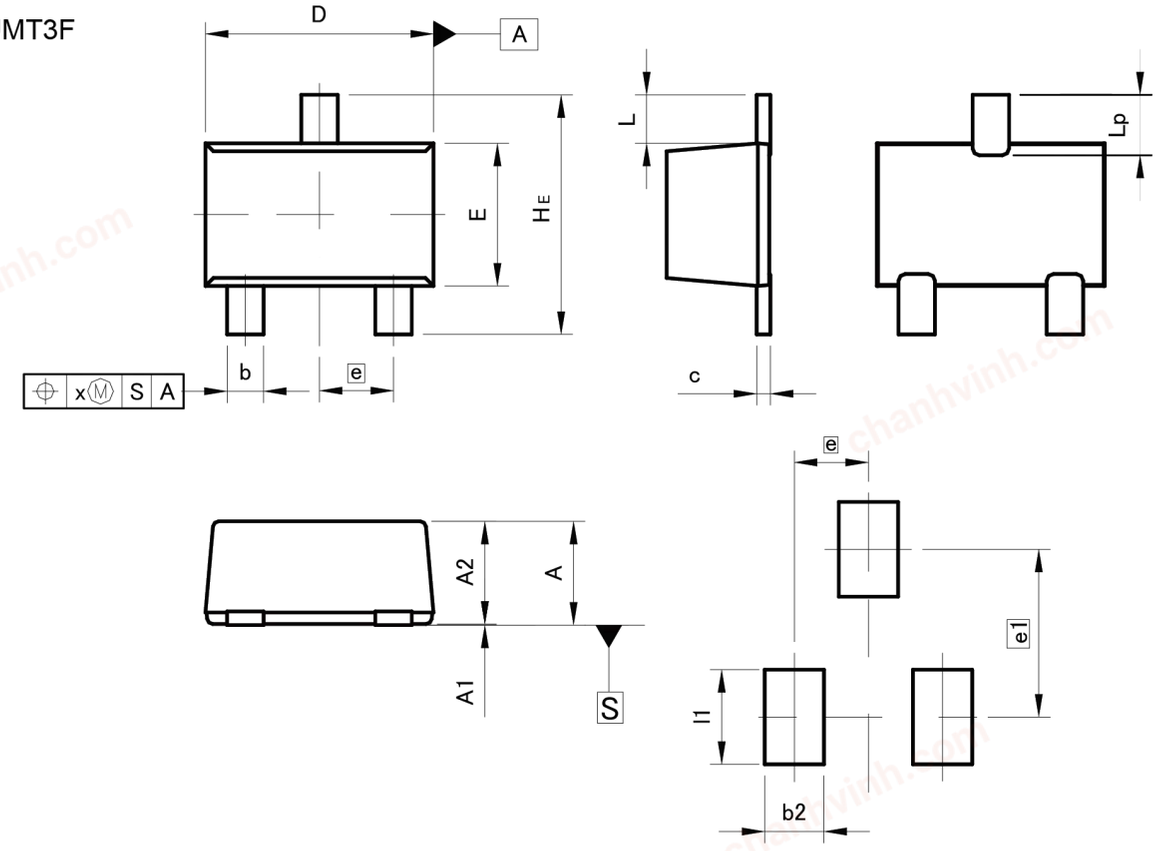
Dimension in mm/inches

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●Dimensions

UMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
c	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L	0.43		0.017	
Lp	0.43	0.63	0.017	0.025
x	–	0.10	–	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	–	0.52	–	0.020
e1	1.47		0.058	
l1	–	0.83	–	0.033

Dimension in mm/inches

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